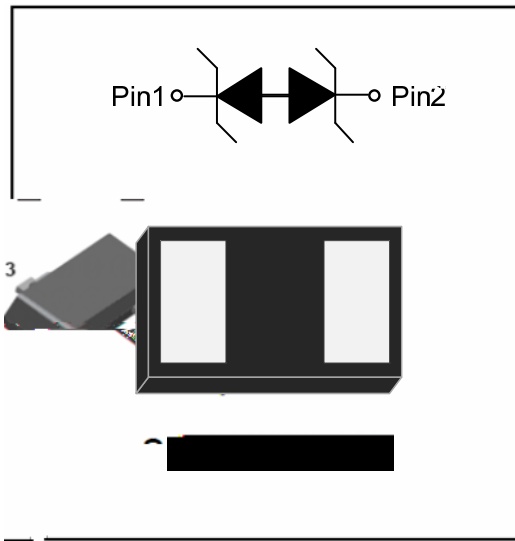


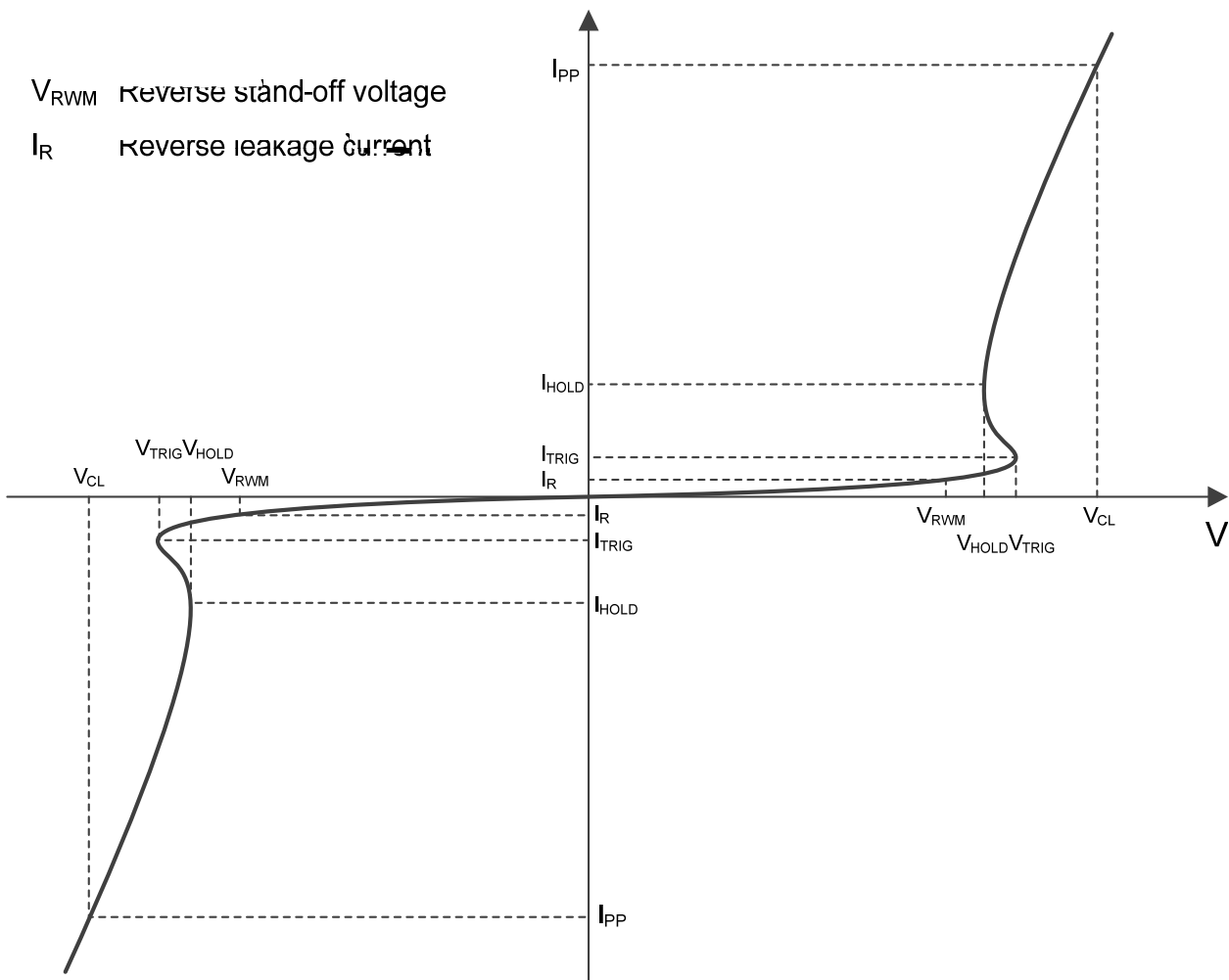


- " Stand-off voltage: $\pm 5.5\text{V}$ Max
- " Transient protection for each line according to
IEC61000-4-2(ESD): $\pm 30\text{kV}$ (contact)
IEC61000-4-4 (EFT): 40A (5/50ns)
IEC61000-4-5(surge): 6A (8/20 s)
- " Ultra-low capacitance: $C_j = 10\text{pF}$ typ
- " Low leakage current
- " Low clamping voltage: $V_{CL} = 11.0\text{V}$ typ. @ $I_{PP} = 16\text{A}$ (TLP)
- " Solid-state silicon technology

- " : DFN1006-2L
- " : Tin plated leads, solderable per
J-STD-002 and JESD22-B102
- " No marking on bi-directional types
- " 6A

V

V_{RWM} Reverse stand-off voltage
 I_R Reverse leakage current





V

Peak pulse power ($t_p = 8/20 \text{ s}$)	P_{pk}	72	W
Peak pulse current ($t_p = 8/20 \text{ s}$)	I_{PP}	6	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	± 30	KV
ESD according to IEC61000-4-2 contact discharge		± 30	KV
Junction temperature	T_J	125	$^{\circ}\text{C}$
Operating temperature	T_{OP}	-40~85	$^{\circ}\text{C}$
Storage temperature	T_{STG}	-55~150	$^{\circ}\text{C}$

V

Ä

Ä

Reverse maximum working voltage	V_{RWM}	V				± 5.5
Reverse leakage current	I_R	nA	$V_{RWM} = 5.5\text{V}$			100
Reverse breakdown voltage	V_{BR}	V	$I_{BR} = 1\text{mA}$	6.1	7	
Reverse holding voltage	V_{HOLD}	V	$I_{HOLD} = 50\text{mA}$	6.1	7	
Clamping voltage ¹⁾	V_{CL}	V	$I_{PP} = 16\text{A}$, $t_p = 100\text{ns}$		11.0	
Dynamic resistance ¹⁾	R_{DYN}				0.28	
Clamping voltage ²⁾	V_{CL}	V	$V_{ESD} = 8\text{kV}$		11.0	
Clamping voltage ³⁾	V_{CL}	V	$I_{PP} = 1\text{A}$, $t_p = 8/20 \text{ s}$			8
		V	$I_{PP} = 6\text{A}$, $t_p = 8/20 \text{ s}$			12
Junction capacitance	C_J	pF	$V_R = 0\text{V}$, $f = 1\text{MHz}$		10	13
		pF	$V_R = 2.5\text{V}$, $f = 1\text{MHz}$		8	11

(1). TLP parameter: $Z_0 = 50 \text{ } \Omega$, $t_p = 100\text{ns}$, $t_r = 2\text{ns}$, averaging window from 60ns to 80ns. R_{DYN} is calculated from 4A to 16A.

(2). Contact discharge mode, according to IEC61000-4-2.

(3). Non-repetitive current pulse, according to IEC61000-4-5.

V

ESD5V5LB	Approximate 0.9	10000	100000	400000	Tape & reel



V

8/20 μ s waveform per IEC61000 # 5

Contact discharge current waveform per IEC61000 # 2

Clamping voltage vs. Peak pulse current

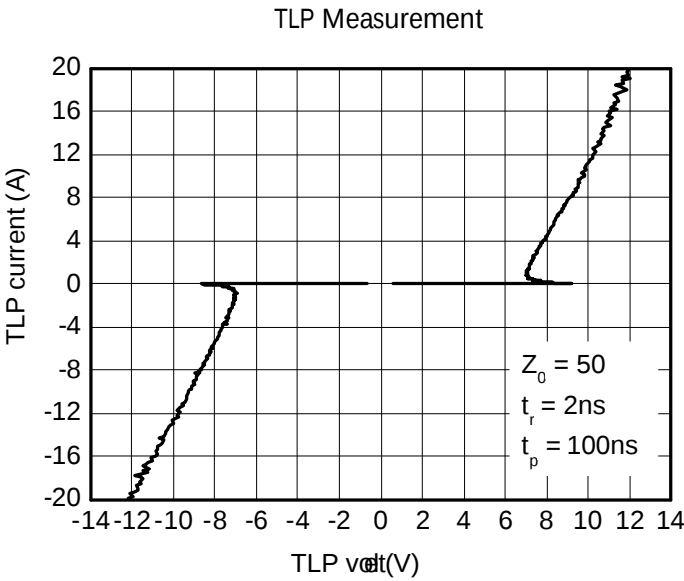
Capacitance vs. Reverse voltage

Non repetitive peak pulse power vs. Pulse time



ESD clamping
(+8kV contact discharge per IEC61000 4 2)

ESD clamping
(8kV contact discharge per IEC61000 4 2)



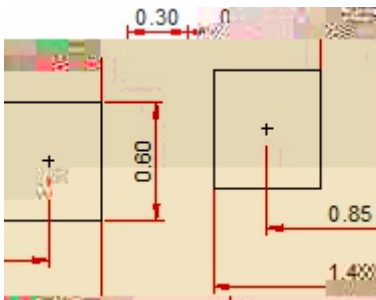
V



6 \ P E R O	P L Q	P P	0 D	P P
\$				
%				
&				
&				
,				
(				
)				
*				



V



Notes:

This recommended land pattern is for reference purposes only. Please consult your manufacturing group to ensure your PCB design guidelines are met



The information presented in this document is for reference only. Yangzhou Yangjie Electronic Technology Co., Ltd. reserves the right to make changes without notice for the specification of the products displayed herein to improve reliability, function or design or otherwise.

The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with equipment or devices which require high level of reliability and the malfunction of which would directly endanger human life (such as medical instruments, transportation equipment, aerospace machinery, nuclear-reactor controllers, fuel controllers and other safety devices), Yangjie or anyone on its behalf, assumes no responsibility or liability for any damages resulting from such improper use of sale.

This publication supersedes & replaces all information previously supplied. For additional information, please visit our website [http:// www.21yangjie.com](http://www.21yangjie.com) , or consult your nearest Yangjie's sales office for further assistance.